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XL2803A SOP18

1 Features

- 500-mA-Rated Collector Current (Single Output)
- High-Voltage Outputs: 50 V
- Output Clamp Diodes
- Inputs Compatible With Various Types of Logic

2 Applications

- Relay Drivers
- Hammer Drivers
- Lamp Drivers
- Display Drivers (LED and Gas Discharge)
- Line Drivers
- Logic Buffers
- Stepper Motors
- IP Camera
- HVAC Valve and LED Dot Matrix

3 Description

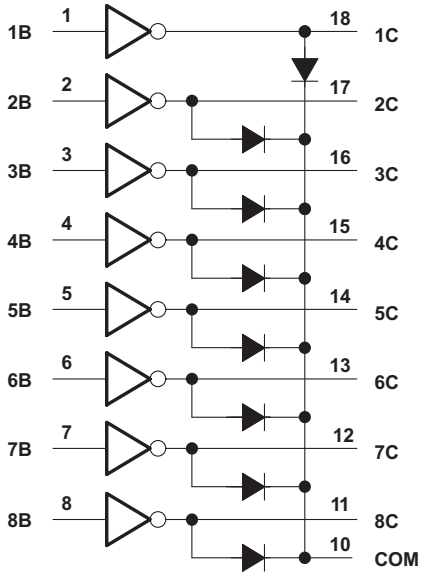
The XL2803A device is a 50 V, 500 mA Darlington transistor array. The device consists of eight NPN Darlington pairs that feature high-voltage outputs with common-cathode clamp diodes for switching inductive loads. The collector-current rating of each Darlington pair is 500 mA. The Darlington pairs may be connected in parallel for higher current capability.

Applications include relay drivers, hammer drivers, lamp drivers, display drivers (LED and gas discharge), line drivers, and logic buffers. The XL2803A device has a 2.7-kΩ series base resistor for each Darlington pair for operation directly with TTL or 5-V CMOS devices.

4 Device Information[1]

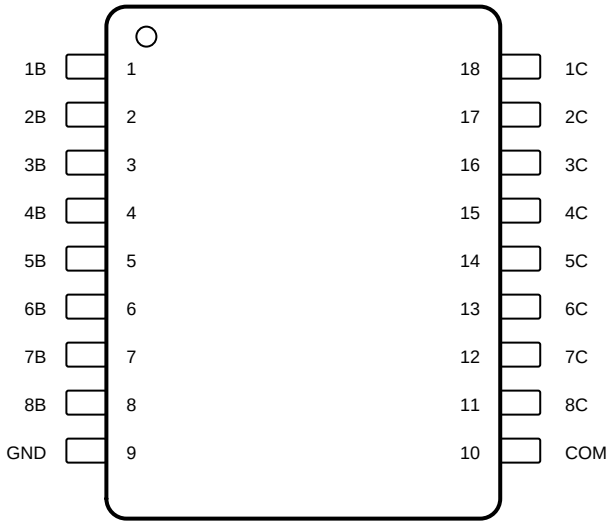
PART NUMBER	PACKAGE	BODY SIZE (NOM)
XL2803A	SOIC (18)	11.55 mm × 7.50 mm

Logic Diagram



5 Pin Configuration and Functions

DW Package
18-Pin SOIC
Top View



Not to scale

Pin Functions

PIN		TYPE	DESCRIPTION
NAME	NO.		
1B	1	I	Channel 1 through 8 Darlington base input
2B	2		
3B	3		
4B	4		
5B	5		
6B	6		
7B	7		
8B	8		
1C	18	O	Channel 1 through 8 Darlington collector output
2C	17		
3C	16		
4C	15		
5C	14		
6C	13		
7C	12		
8C	11		
GND	9	—	Common emitter shared by all channels (typically tied to ground)
COM	10	I/O	Common cathode node for flyback diodes (required for inductive loads)

6 Specifications

6.1 Absolute Maximum Ratings

at 25°C free-air temperature (unless otherwise noted)(1)

		MIN	MAX	UNIT
V_{CE}	Collector-emitter voltage		50	V
V_I	Input voltage(2)		30	V
	Peak collector current		500	mA
I(clamp)	Output clamp current		500	mA
	Total substrate-terminal current		–2.5	A
T_J	Junction temperature	–65	150	°C
T_{stg}	Storage temperature	–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltage values, unless otherwise noted, are with respect to the emitter/substrate terminal GND.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±2000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101(2)	±500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V_{CE}	Collector-emitter voltage	0	50	V
T_A	Ambient temperature	–40	85	°C

6.4 Thermal Information

THERMAL METRIC(1)		XL2803A DW (SOIC) 18 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	66.4	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	29.5	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	33.0	°C/W
ψ_{JT}	Junction-to-top characterization parameter	6.0	°C/W
ψ_{JB}	Junction-to-board characterization parameter	32.5	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

6.5 Electrical Characteristics

at T_A = 25°C free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS		XL2803A			UNIT
				MIN	TYP	MAX	
I_{CEX}	Collector cutoff current	V_{CE} = 50 V, see Figure 3	I_I = 0			50	μA
$I_{I(off)}$	Off-state input current	V_{CE} = 50 V, T_A = 70°C	I_C = 500 μA, see Figure 4	50	65		μA
$I_{I(on)}$	Input current	V_I = 3.85 V,	See Figure 5		0.93	1.35	mA
$V_{I(on)}$	On-state input voltage	V_{CE} = 2 V, see Figure 6	I_C = 200 mA			2.4	V
			I_C = 250 mA			2.7	
			I_C = 300 mA			3	
$V_{CE(sat)}$	Collector-emitter saturation voltage	I_I = 250 μA, see Figure 7	I_C = 100 mA		0.9	1.1	V
		I_I = 350 μA, see Figure 7	I_C = 200 mA		1	1.3	
		I_I = 500 μA, see Figure 7	I_C = 350 mA		1.3	1.6	
I_R	Clamp diode reverse current	V_R = 50 V,	see Figure 8			50	μA
V_F	Clamp diode forward voltage	I_F = 350 mA	see Figure 9		1.7	2	V
C_i	Input capacitance	V_I = 0,	f = 1 MHz		15	25	pF

6.6 Switching Characteristics

T_A = 25°C

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH}	Propagation delay time, low- to high-level output	V_S = 50 V, C_L = 15 pF, R_L = 163 Ω, See Figure 10		130		ns
t_{PHL}	Propagation delay time, high- to low-level output			20		
V_{OH}	High-level output voltage after switching	V_S = 50 V, I_O = 300 mA, see Figure 11	V_S – 20			mV

6.7 Typical Characteristics

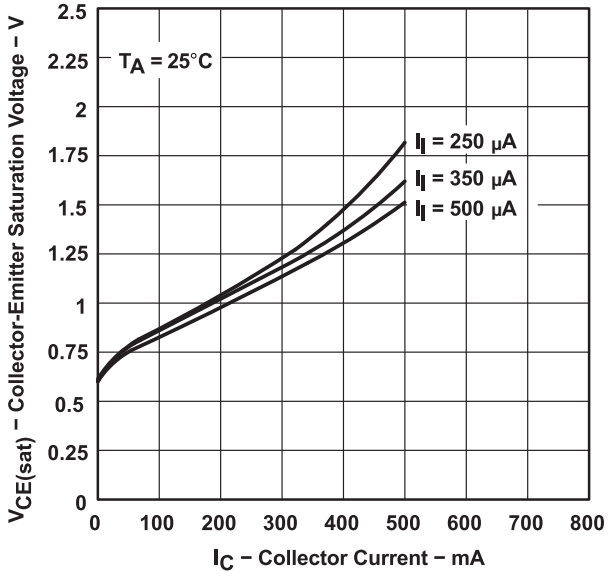


Figure 1. Collector-Emitter Saturation Voltage vs Collector Current (One Darlington)

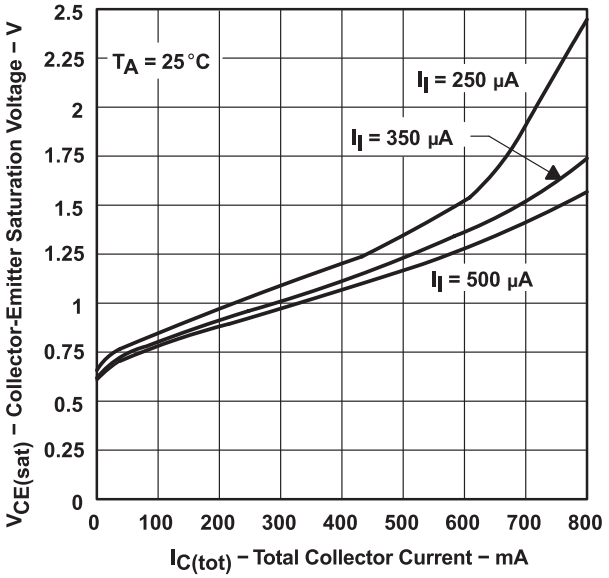


Figure 2. Collector-Emitter Saturation Voltage vs Total Collector Current (Two Darlingtons in Parallel)

7 Parameter Measurement Information

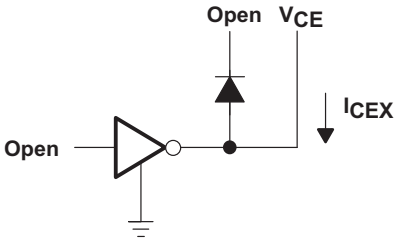


Figure 3. I_{CEX} Test Circuit

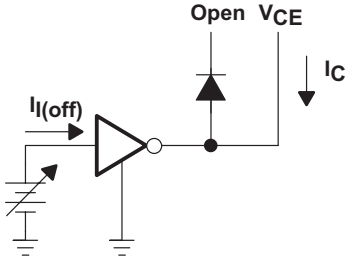


Figure 4. $I_{I(off)}$ Test Circuit

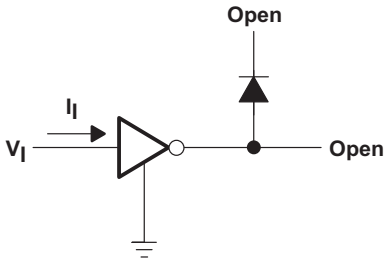


Figure 5. $I_{I(on)}$ Test Circuit

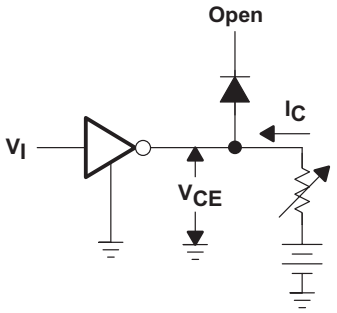


Figure 6. $V_{I(on)}$ Test Circuit

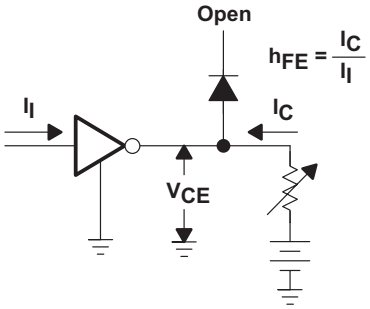


Figure 7. h_{FE}, $V_{CE(sat)}$ Test Circuit

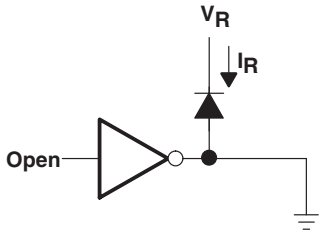


Figure 8. I_R Test Circuit

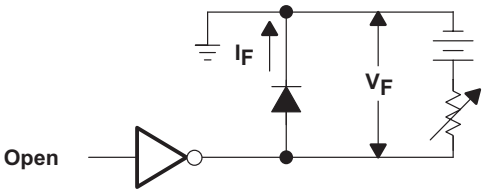
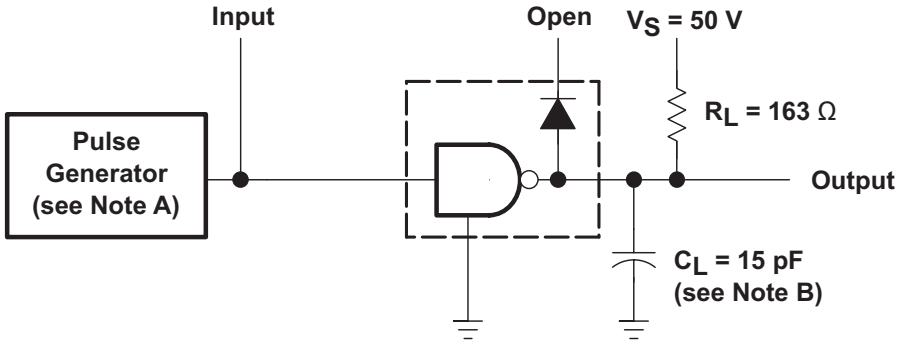
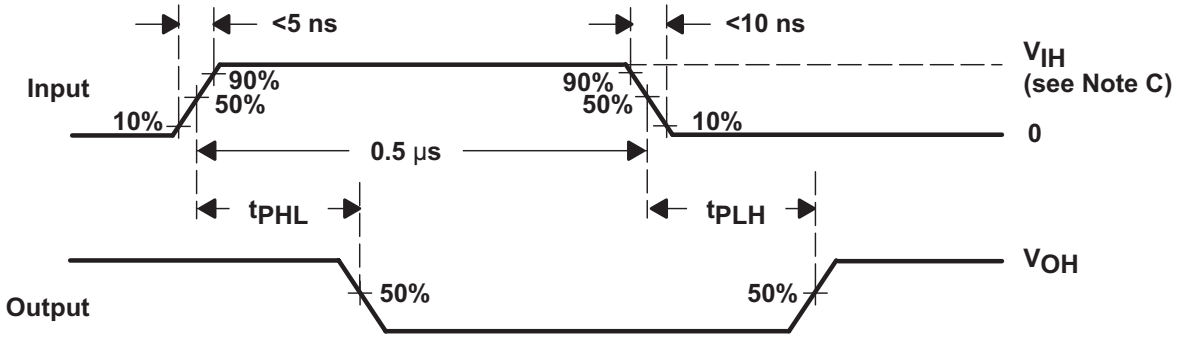


Figure 9. V_F Test Circuit

Parameter Measurement Information (continued)



Test Circuit



Voltage Waveforms

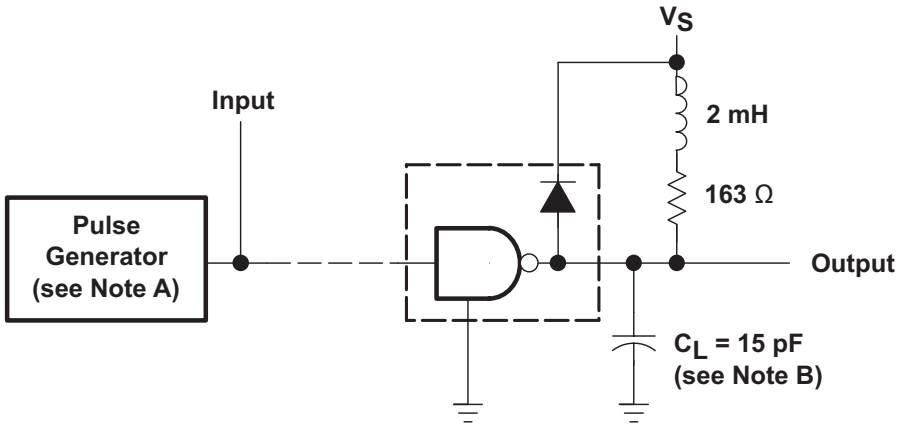
A. The pulse generator has the following characteristics: PRR = 12.5 kHz, Z_O = 50 Ω.

B. C_L includes probe and jig capacitance.

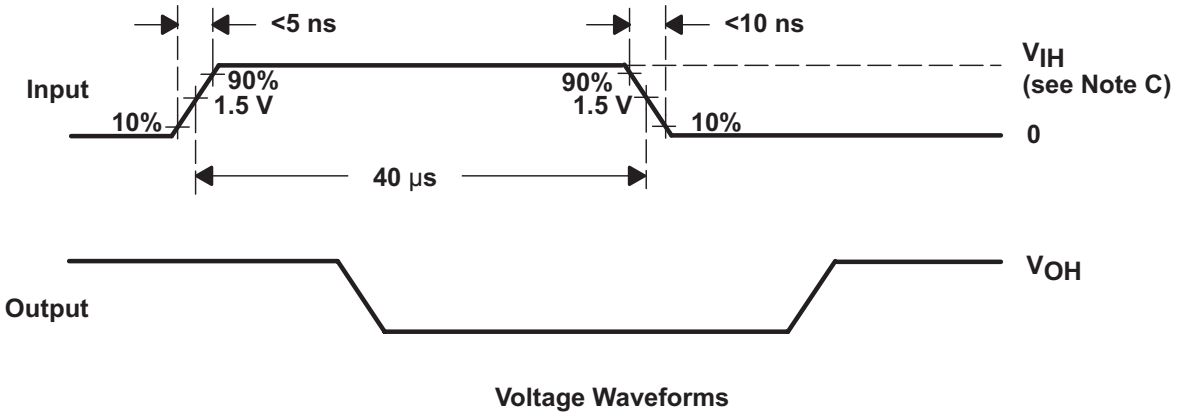
C. V_{IH} = 3 V

Figure 10. Propagation Delay Times

Parameter Measurement Information (continued)



Test Circuit



Voltage Waveforms

A. The pulse generator has the following characteristics: PRR = 12.5 kHz, Z_O = 50 Ω.

B. C_L includes probe and jig capacitance.

C. V_{IH} = 3 V

Figure 11. Latch-Up Test

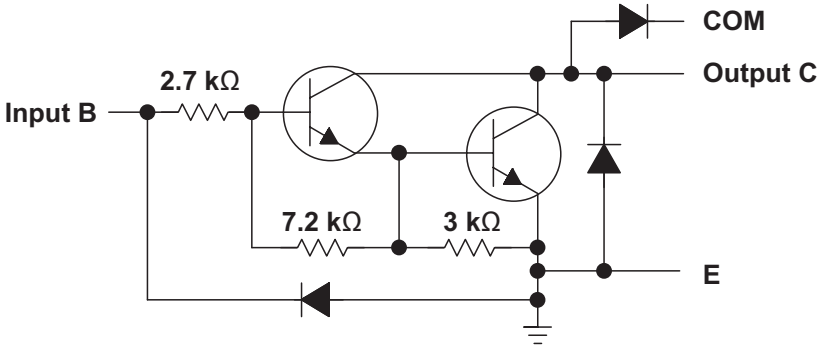
8 Detailed Description

8.1 Overview

This standard device has proven ubiquity and versatility across a wide range of applications. This is due to its integration of 8 Darlington transistors that are capable of sinking up to 500 mA and wide GPIO range capability.

The XL2803A is comprised of eight high voltage, high current NPN Darlington transistor pairs. All units feature a common emitter and open collector outputs. To maximize their effectiveness, these units contain suppression diodes for inductive loads. The XL2803A has a series base resistor to each Darlington pair, thus allowing operation directly with TTL or CMOS operating at supply voltages of 5 V or 3.3 V. The XL2803A offers solutions to a great many interface needs, including solenoids, relays, lamps, small motors, and LEDs. Applications requiring sink currents beyond the capability of a single output may be accommodated by paralleling the outputs.

8.2 Functional Block Diagram



8.3 Feature Description

Each channel of XL2803A consists of Darlington connected NPN transistors. This connection creates the effect of a single transistor with a very-high current gain. The very high β allows for high output current drive with a very-low input current, essentially equating to operation with low GPIO voltages.

The GPIO voltage is converted to base current through the 2.7-kΩ resistor connected between the input and base of the predriver Darlington NPN.

The diodes connected between the output and COM pin are used to suppress the kick-back voltage from an inductive load that is excited when the NPN drivers are turned off (stop sinking) and the stored energy in the coils causes a reverse current to flow into the coil supply through the kick-back diode.

In normal operation, the diodes on base and collector pins to emitter will be reverse biased. If these diode are forward biased, internal parasitic NPN transistors will draw (a nearly equal) current from other (nearby) device pins.

8.4 Device Functional Modes

8.4.1 Inductive Load Drive

When the COM pin is tied to the coil supply voltage, XL2803A is able to drive inductive loads and suppress the kick-back voltage through the internal free wheeling diodes.

8.4.2 Resistive Load Drive

When driving resistive loads, COM can be left unconnected or connected to the load voltage supply. If multiple supplies are used, connect to the highest voltage supply.

9 Application and Implementation

9.1 Application Information

XL2803A will typically be used to drive a high voltage and/or current peripheral from an MCU or logic device that cannot tolerate these conditions. The following design is a common application of XL2803A, driving inductive loads. This includes motors, solenoids, and relays. Each load type can be modeled by what is seen in Figure 12.

9.2 Typical Application

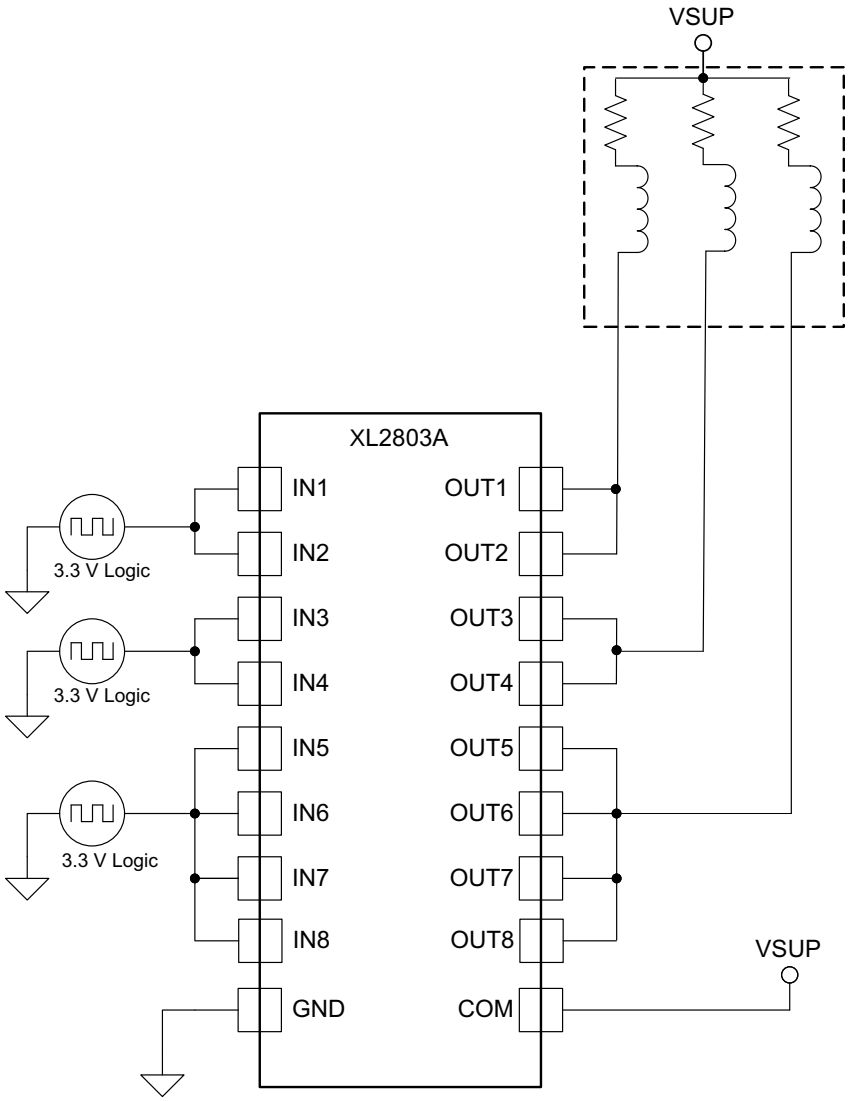


Figure 12. XL2803A as Inductive Load Driver

Typical Application (continued)

9.2.1 Design Requirements

For this design example, use the parameters listed in Table 1 as the input parameters.

Table 1. Design Parameters

DESIGN PARAMETER	EXAMPLE VALUE
GPIO voltage	3.3 or 5 V
Coil supply voltage	12 to 50 V
Number of channels	8
Output current (R_{COIL})	20 to 300 mA per channel
Duty cycle	100%

9.2.2 Detailed Design Procedure

When using XL2803A in a coil driving application, determine the following:

- Input voltage range
- Temperature range
- Output and drive current
- Power dissipation

9.2.2.1 Drive Current

The coil current is determined by the coil voltage (VSUP), coil resistance, and output low voltage (V_{OL} or $V_{CE(SAT)}$).

$$I_{COIL} = (V_{SUP} - V_{CE(SAT)}) / R_{COIL} \quad (1)$$

9.2.2.2 Output Low Voltage

The output low voltage (V_{OL}) is the same thing as $V_{CE(SAT)}$ and can be determined by Figure 1, Figure 2, or *Electrical Characteristics*.

9.2.2.3 Power Dissipation and Temperature

The number of coils driven is dependent on the coil current and on-chip power dissipation. To determine the number of coils possible, use Equation 2 to calculate XL2803A on-chip power dissipation P_D.

$$P_D = \sum_{i=1}^{N} V_{OLi} \times I_{Li}$$

where

- N is the number of channels active together.
- V_{OLi} is the OUT_i pin voltage for the load current I_{Li}. This is the same as $V_{CE(SAT)}$ (2)

To ensure the reliability of XL2803A and the system, the on-chip power dissipation must be lower that or equal to the maximum allowable power dissipation (P_D) dictated by Equation 3.

$$PD_{(MAX)} = \left(T_{J(MAX)} - T_A\right) \Big/ \theta_{JA}$$

where

- $T_{J(MAX)}$ is the target maximum junction temperature.
- T_A is the operating ambient temperature.
- θ_{JA} is the package junction to ambient thermal resistance. (3)

9.2.3 Application Curves

The following curves were generated with XL2803A driving an OMRON G5NB relay – V_{in} = 5.0 V; V_{sup}= 12 V and R_{COIL}= 2.8 kΩ

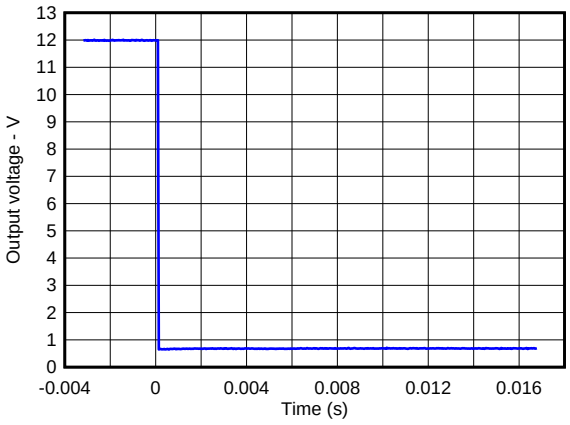


Figure 13. Output Response With Activation of Coil (Turn On)

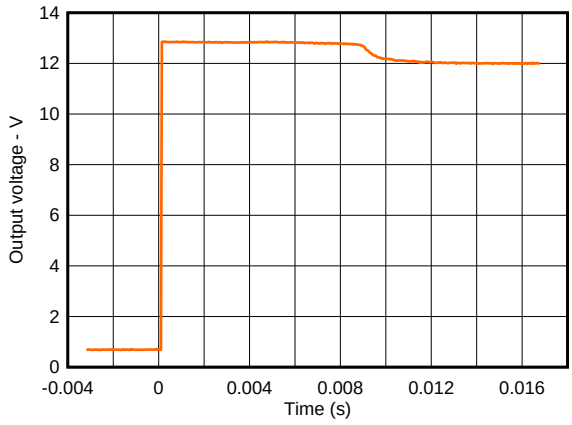


Figure 14. Output Response With De-Activation of Coil (Turn Off)

10 Power Supply Recommendations

This part does not need a power supply; however, the COM pin is typically tied to the system power supply. When this is the case, make sure that the output voltage does not heavily exceed the COM pin voltage. This will heavily forward bias the flyback diodes and cause a large current to flow into COM, potentially damaging the on-chip metal or overheating the part.

11 Layout

11.1 Layout Guidelines

Thin traces can be used on the input due to the low current logic that is typically used to drive XL2803A. Take care to separate the input channels as much as possible, as to eliminate crosstalk. TI recommends thick traces for the output, in order to drive high currents as desired. Wire thickness can be determined by the trace material's current density and desired drive current.

Because all of the channels currents return to a common emitter, it is best to size that trace width to be very wide. Some applications require up to 2.5 A.

11.2 Layout Example

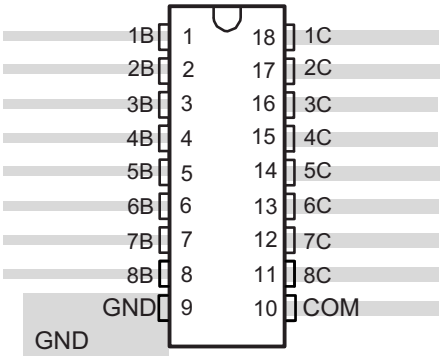
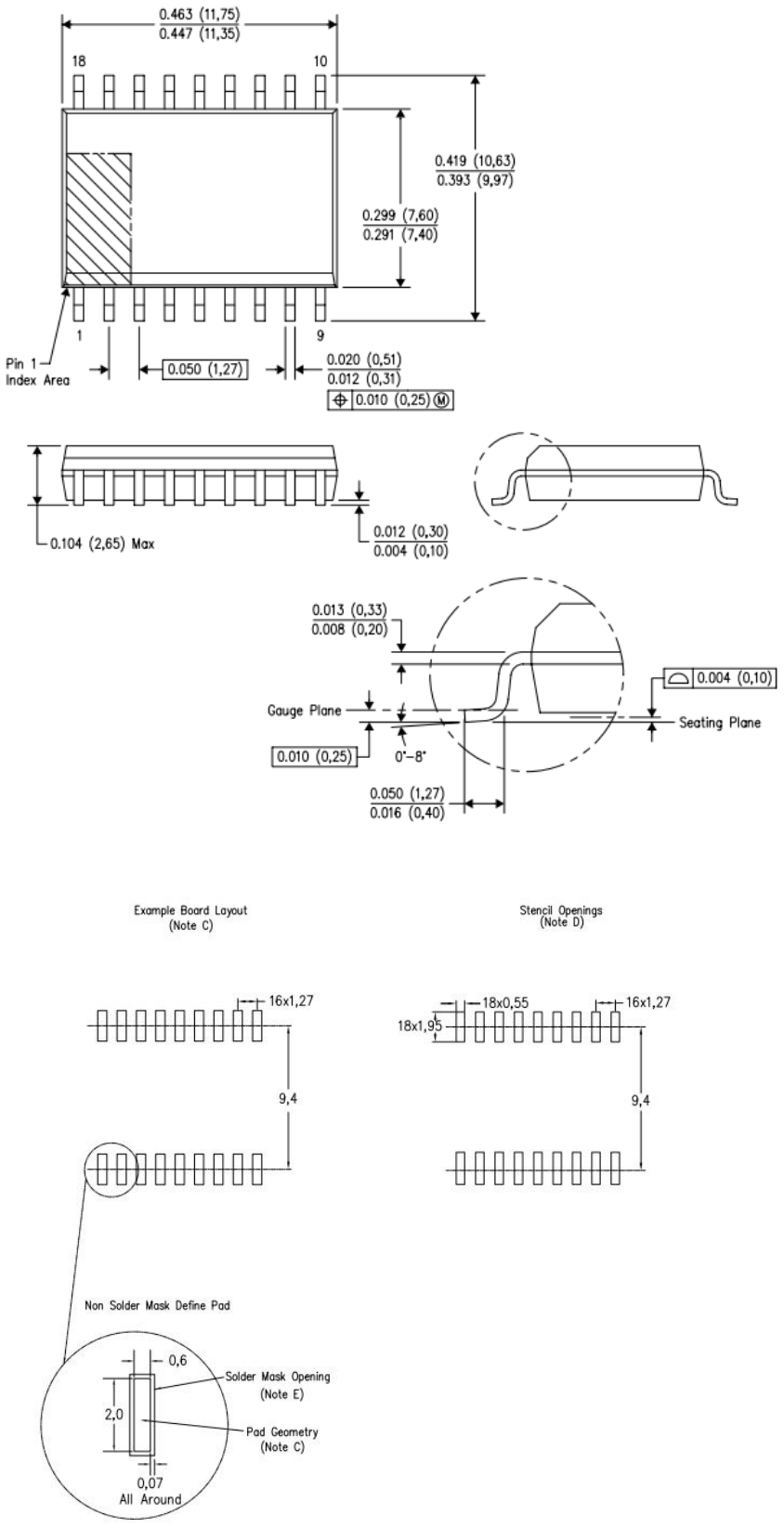


Figure 15. Package Layout



以上信息仅供参考.如需帮助联系客服人员。谢谢 XINLUDA